

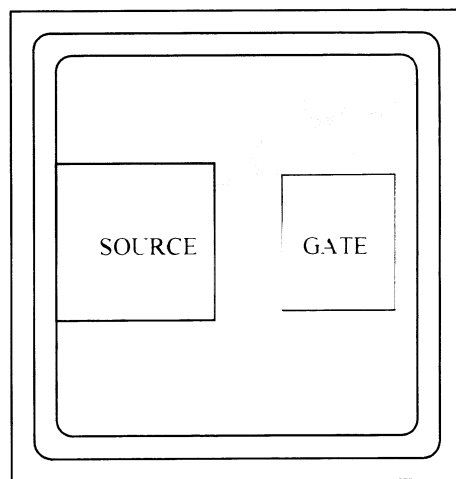


# Sierra Components, Inc.

2222 Park Place • Suite 3E • Minden, Nevada 89423

Phone: 775.783.4940 Fax: 775.783.4947

## PAD FUNCTIONS



**N-Channel Enhancement Mode MOS Transistor**

The information given is believed to be correct at the time of issue.

Please verify your requirements prior to commencement of any assembly process, as no liability for omission or error can be accepted.

Back potential is the electrical potential of the substrate (bulk silicon) which does not require an electrical connection unless stated in this drawing.

**Note: 1 mil = 0.001inch**

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|---|---|--|
| <p><u>APPROVED</u></p> <p>GB</p> <p>.....</p> <p>DATE: 19.08.10</p> | <p style="text-align: center;"><b>VNDQ1</b></p> <p style="text-align: center;"><b>SILICONIX</b></p> | <p style="text-align: center;"><u>DIE INFORMATION</u></p> <p>DIMENSIONS (Mils): 38 x 38</p> <p>BOND PADS (Mils):</p> <p>MASK REF:</p> <p>GEOMETRY:</p> <p>BACK POTENTIAL DRAIN</p> |
| <p><u>SERIAL NUMBER</u></p> <p>M000245</p>                          |   | <p style="text-align: center;"><u>METALLISATION</u></p> <p>TOP: Al</p> <p>BACK: Au</p>   |